L Number	Hits	Search Text	DB	Time stamp
1	622	(semiconductor wafer) near blad	USPAT; US-PGPUB; EP ; JP ; DERWENT; IBM_TDB	2003/10/17 14:42
2	1399972	(semiconductor wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 14:42
3	110214	((semiconductor wafer)) and sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/10/17 14:43
4	7687	(((semiconductor wafer)) and sensor) and strain	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 14:43
5	1985	((((semiconductor wafer)) and sensor) and strain) and (piezoelectric piezo-electric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 14:44
6	7	(((((semiconductor wafer)) and sensor) and strain) and (piezoelectric piezo-electric)) and 294/\$.ccis.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 14:54
7	35	("Re28663" "1315581" "3353860" "3370213" "3491520" "3625378" "3827437" "4130314" "4540211" "4544193" "4552397" "4565400" "4579380" "4590673" "4610475" "4667997" "4671553" "4694230" "4696501" "4699414" "4723806" "4735451" "4796357" "4808898" "4813732" "4816730" "4819978" "4828309" "4872803" "4898416" "4955656" "4976484" "5046773" "5080415" "5163804").PN.	USPAT	2003/10/17 14:49
8	13	(((((semiconductor wafer)) and sensor) and strain) and (piezoelectric plezo-electric)) and 414/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 15:02
9	7	("4610475" "4642438" "4667997" "5100502" "5438419" "5511931" "5641264").PN.	USPAT	2003/10/17 14:59

10	50	(((((semic nductor wafer)) and sens r) and	USPAT;	2003/10/17	
10		strain) and (piezo lectric pi zo-el ctric))	US-P PUB;	15:14	
		and 29/\$.ccls.	EP ; JP ;		
			DERWENT;		1
11	10	 ("4674186" "5266801" "5325081"	IBM_TDB USPAT	2003/10/17	
11	10	(4674166 5266601 5325661	USPAT	15:06	
		"5468959" "5469733" "5907095"		10.00	
		"6072247").PN.			Ì
12	502	(((((semiconductor wafer)) and sensor) and	USPAT;	2003/10/17	
		strain) and (plezoelectric piezo-electric))	US-PGPUB;	15:15	
		and 73/\$.ccls.	EPO; JPO;		
			DERWENT;		ŀ
			IBM_TDB		
13	123	((((((semiconductor wafer)) and sensor) and	USPAT;	2003/10/17	
		strain) and (plezoelectric plezo-electric))	US-PGPUB;	15:15	
		and 73/\$.ccis.) and micro	EPO; JPO;		
			DERWENT; IBM_TDB		
_	1	chun-keng near hsu	USPAT;	2002/11/04	
-	•	Chull-Keng hear hou	US-PGPUB;	10:36	l
			EPO; JPO;		
			DERWENT;		
			IBM_TDB		
-	0	tin-hau near kuo	USPAT;	2002/11/04	
			US-PGPUB;	10:36	
			EPO; JPO;		
			DERWENT;		
			IBM_TDB		
-	1	chun-chih near lin	USPAT;	2002/11/04	-
			US-PGPUB;	10:36	
		1 8 1	EPO; JPO; DERWENT;		-
			IBM_TDB		-
_	2	chao-lin near lee	USPAT;	2002/11/04	
			US-PGPUB;	10:37	
			EPO; JPO;		
			DERWENT;		
			IBM_TDB		
-	432	wafer near blade	USPAT;	2002/11/04	
			US-PGPUB;	11:15	
			EPO; JPO;		
			DERWENT;		
	4430743	company	IBM_TDB	2002/44/04	
-	1128713	sensor	USPAT; US-PGPUB;	2002/11/04 13:30	
			EPO; JPO;	13:30	
			DERWENT;		
			IBM_TDB		
1		i	,	i e	

•	3798	sens r near strain	USPAT;	2002/11/04
÷			US-P PUB;	10:38
			EP;JP;	
			DERWENT;	
			IBM_TDB	
-	787	(sensor near strain) and (piez electric r	USPAT;	2002/11/04
		piezo-electric or piezo)	US-PGPUB;	10:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	73	(sensor near strain) near (piezoelectric or	USPAT;	2002/11/04
		piezo-electric or piezo)	US-PGPUB;	10:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(wafer near blade) and ((sensor near strain)	USPAT;	2002/11/04
		and (piezoelectric or piezo-electric or	US-PGPUB;	10:39
		piezo))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	134	(wafer near blade) and sensor	USPAT;	2002/11/04
			US-PGPUB;	10:39
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	10	((wafer near blade) and sensor) and	USPAT;	2002/11/04
		(piezoelectric)	US-PGPUB;	11:15
		"	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
.	7	("4610475" "4642438" "4667997"	USPAT	2002/11/04
		"5100502" "5438419" "5511931"		11:11
		"5641264").PN.		
_	3	"6113165"	USPAT	2002/11/04
				11:11
_	21	("4040736" "4093378" "5044752"	USPAT	2002/11/04
		"5103367" "5173832" "5400209"		11:11
		"5436790" "5444342" "5444597"		
		"5445486" "5556147" "5645391"		
		"5669752" "5841515" "5842491"		
		"5863170" "5867359" "5872694"		
		"5885355" "5903123" "5948986"). PN .		
_	4471	wafer near chuck	USPAT;	2002/11/04
		Taill Hour Glidon	US-PGPUB;	11:15
			EPO; JPO;	
			DERWENT;	
		'	IBM TDB	
	170	(water maar abunk) and (nicresisetrie)	_	2002/11/04
•	170	(wafer near chuck) and (piezoelectric)	USPAT;	2002/11/04 11:15
			US-PGPUB;	11119
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	1

-	97	((wafer near chuck) and (piezo lectric)) and	USPAT;	2002/11/04
		sensor	US-P PUB;	11:16
			EP ; JPO;	
			DERWENT;	
			IBM_TDB	
-	77	(((wafer near chuck) and (piezoelectric))	USPAT;	2002/11/04
		and sensor) and (alarm signal)	US-PGPUB;	13:23
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3	(((wafer near chuck) and (piezoelectric))	USPAT;	2002/11/04
		and sensor) and (alarm)	US-PGPUB;	13:24
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	134	(wafer near blade) and sensor	USPAT;	2002/11/04
		,	US-PGPUB;	13:30
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	7	((wafer near blade) and sensor) and alarm	USPAT;	2002/11/04
•	•	((Water flear blade) and Sensor) and alarm	US-PGPUB;	13:30
			EPO; JPO;	13.30
			DERWENT;	
			IBM_TDB	
	F250		USPAT;	2002/11/04
-	5358	strain near gage	1	14:56
			US-PGPUB;	14:50
			EPO; JPO;	
			DERWENT;	
	070	(-tu-lu unan unan) and (unafan	IBM_TDB	2002/44/04
-	878	(strain near gage) and (wafer	USPAT;	2002/11/04
		semiconductor)	US-PGPUB;	14:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	000044/04
-	1424	(strain near (sensor or gage)) and (wafer	USPAT;	2002/11/04
		semiconductor)	US-PGPUB;	14:57
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2000/44/54
-	68	(strain near (sensor or gage)) and (wafer	USPAT;	2002/11/04
		semiconductor) and blade	US-PGPUB;	14:58
			EPO; JPO;	
			DERWENT;	
		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	IBM_TDB	
-	2	("6494882").PN.	USPAT;	2003/08/12
			US-PGPUB;	12:45
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

US-PGPUB; EP; JP; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO, JPO; DERWENT; ISM, TDB USPAT; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB		28565	strain near (sens r gauge)	USPAT;	2003/08/12
EP ; JP ; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; I	-	20303	Strain near (sens i gauge)		
- 465244 thin same film				•	12.40
BM_TDB					
- 605 (wafer semiconductor) near blade USPAT; US-PGPUB; EPC; JPO; DERWENT; IBM TDB USPAT; US-PGFUB; EPC; JPO; DERWENT; IBM TDB USPAT; US-PGFUB; EPC; JPO; DERWENT; IBM_TDB USPAT; US-PGFUB; EPC; JPO; JPO; DERWENT; IBM_TDB USPAT;					
US-PGPUB; EPO, JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB;		COF	(wefer coming advetor) near blade		2002/09/42
- 465244 thin same film	-	605	(water semiconductor) near blade	_	
- 465244 thin same film				1	12:40
Martin M					
- 465244 thin same film					
US-PGPUB; EPC; JPC; DERWENT; IBM_TDB USPAT; Semiconductor) near blade US-PGPUB; EPC; JPC; DERWENT; IBM_TDB USPAT; Sensitive US-PGPUB; EPC; JPC; DERWENT; IBM_TDB USPAT; Sensitive US-PGPUB; EPC; JPC; DERWENT; IBM_TDB USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB USPAT; Sensitive US-PGPUB; EPC; JPC; DERWENT; IBM_TDB USPAT; Sensitive US-PGPUB; EPC; JPC; DERWENT; IBM_TDB US-PGPU		400044		_	0000/00/40
Strain near (sensor gauge) and ((wafer semiconductor) near blade) Strain near (sensor gauge) Strain near (sensor sensing sensitive) Strain near (sensor	-	465244	thin same film	,	
- 4 (strain near (sensor gauge)) and ((wafer semiconductor) near blade) - 5807 plezoelectric near (sensor sensing sensitive) - 584 (strain near (sensor gauge)) and (plezoelectric near (sensor sensing sensitive)) - 584 (strain near (sensor gauge)) and (plezoelectric near (sensor sensing sensitive)) - 5 ("4502857" "5043111" "5174933" US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; IS-PGPUB; EPO; JPO; IS-PGPUB; EPO; JPO; IS-PGPUB; IS-P				•	12:46
A (strain near (sensor gauge)) and ((wafer semiconductor) near blade)					
. 4 (strain near (sensor gauge)) and ((wafer semiconductor) near blade) - 5807 plezoelectric near (sensor sensing sensitive) - 584 (strain near (sensor gauge)) and (plezoelectric near (sensor sensing sensitive)) - 584 (strain near (sensor gauge)) and (plezoelectric near (sensor sensing sensitive)) - 5 ("4502857" "5043111" "5174933" USPAT; USPGPUB; Sensitive)) - 145 (73/767).CCLS. - 17035 sensitivity and 73/\$.ccls. - 468 (sensitivity and 73/\$.ccls.) and (strain near sensor) - 162268 73/\$.ccls. - 162268 73/\$.ccls. - 162268 73/\$.ccls.					
Semiconductor) near blade US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; 12:49 US-PGPUB; 12:50 US-PGPUB; 12:50 US-PGPUB; 12:50 US-PGPUB; 12:50 US-PGPUB; 12:50 US-PGPUB; 13:31 US-PAT; US-PGPUB; 13:31 2003/08/12 13:31 2003/08/25 13:13 US-PAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PAT; US-PGPUB; US-PGP				-	
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPA	-	4	·		
DERWENT; IBM_TDB USPAT; 2003/08/12 12:49 - S84 (strain near (sensor gauge)) and (plezoelectric near (sensor sensing sensitive)) - S84 (strain near (sensor gauge)) and (plezoelectric near (sensor sensing sensitive)) - S64 ("4502857" "5043111" "5174933" USPAT; IBM_TDB USPAT 2003/08/12 12:50 - S67 ("4502857" "5043111" "5174933" USPAT 2003/08/12 13:31 - S67 ("73/767).CCLS.			semiconductor) near blade)	1	12:48
- 5807 plezoelectric near (sensor sensing sensitive) - 584 (strain near (sensor gauge)) and (plezoelectric near (sensor sensing sensitive)) - 584 (strain near (sensor gauge)) and (plezoelectric near (sensor sensing sensitive)) - 5 ("4502857" "5043111" "5174933" US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO;					
- \$587 plezoelectric near (sensor sensing sensitive) Sensitive US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; U					
Sensitive US-PGPUB; EPG; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT				_	
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT 2003/08/12 12:50 5 ("4502857" "5043111" "5174933" USPAT 2003/08/12 13:31 - 145 (73/767).CCLS. USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; ISPGPUB; EPO; JPO; JESSE EPO; JESSE EPO; JESSE EPO; JPO; JESSE EPO; JPO; JESSE EPO; JESSE	-	5807	piezoelectric near (sensor sensing		2003/08/12
DERWENT; IBM_TDB USPAT; 2003/08/12 12:50 EPO; JPO; DERWENT; IBM_TDB USPAT; 12:50 EPO; JPO; DERWENT; IBM_TDB USPAT 2003/08/12 13:31 USPAT; 13:31 USPAT; 2003/08/12 13:31 USPAT; 2003/08/25 USPAT;			sensitive)	US-PGPUB;	12:49
S84 (strain near (sensor gauge)) and (piezoelectric near (sensor sensing sensitive)) SPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT 2003/08/12 12:50				1	
- 162268 73/\$.ccls. USPAT; USPAPPUB; EPO; JPO;				DERWENT;	
(piezoelectric near (sensor sensing sensitive)) (piezoelectric near (sensor) sensitive) (piezoelectric near (sensor) sensor) (piezoelectric				IBM_TDB	
Sensitive)) EPO; JPO; DERWENT; IBM_TDB USPAT 145 ("4502857" "5043111" "5174933" USPAT "5528452" "6294113").PN. 145 (73/767).CCLS. USPAT; USPGPUB; EPO; JPO; USPAT; U	-	584	(strain near (sensor gauge)) and	USPAT;	2003/08/12
- 17035 sensitivity and 73/\$.ccls. - 468 (sensitivity and 73/\$.ccls.) and (strain near sensor) - 162268 73/\$.ccls. DERWENT; IBM_TDB USPAT 2003/08/12 13:31 2003/08/25 13:13 2003/08/25 13:13 2003/08/25 13:13 2003/08/25 13:15 2003/08/25 13:16 2003/08/25 13:16 2003/08/25 13:16 2003/08/25 13:15 2003/08/25 2003/08/25 2003/08/25 2003/08/25 2			(piezoelectric near (sensor sensing	US-PGPUB;	12:50
- ("4502857" "5043111" "5174933" USPAT 2003/08/12 13:31 2003/08/12 13:31 2003/08/25 13:13 USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB;			sensitive))	EPO; JPO;	
- 145 ("4502857" "5043111" "5174933" USPAT 2003/08/12 13:31 2003/08/25 13:13 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; DERWENT; ISPGPUB; EPO; JPO; US-PGPUB; US-PGPUB				DERWENT;	
- 145 (73/767).CCLS. 13:31 2003/08/25 13:13 2003/08/25 13:13 2003/08/25 13:13 2003/08/25 13:13 2003/08/25 13:13 2003/08/25 13:13 2003/08/25 13:16 2003/08/25 2003/08/2	•		•	IBM_TDB	
- 145 (73/767).CCLS. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; US-PGPUB; EPO;	-	5	("4502857" "5043111" "5174933"	USPAT	2003/08/12
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; ISM_TDB US-PGPUB; EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J			"5528452" "6294113").PN.		13:31
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; I5:56	-	145	(73/767).CCLS.	USPAT;	2003/08/25
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO;				US-PGPUB;	13:13
- 17035 sensitivity and 73/\$.ccls. sensitivity and 73/\$.ccls. 468 (sensitivity and 73/\$.ccls.) and (strain near sensor) (sensor) 162268 73/\$.ccls. IBM_TDB USPAT; US-PGPUB; EPO; JPO; USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; USPAT; US-PGPUB; USPAT; US-PGPUB; EPO; JPO; EPO;				EPO; JPO;	
- 17035 sensitivity and 73/\$.ccls. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;				DERWENT;	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO;				IBM_TDB	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO;	•	17035	sensitivity and 73/\$.ccls.	USPAT;	2003/08/25
- 468 (sensitivity and 73/\$.ccls.) and (strain near sensor) - 162268 73/\$.ccls. DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;					13:16
- 468 (sensitivity and 73/\$.ccls.) and (strain near sensor) - 162268 73/\$.ccls. 162268 73/\$.ccls. 18M_TDB 2003/08/25 13:15 13:15				EPO; JPO;	
- 468 (sensitivity and 73/\$.ccls.) and (strain near sensor) - 162268 73/\$.ccls. 162268 73/\$.ccls. 18M_TDB 2003/08/25 13:15 13:15				DERWENT;	
- 468 (sensitivity and 73/\$.ccls.) and (strain near sensor) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO;				· ·	
sensor) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; US-PGPUB; EPO; JPO; 13:15	-	468	(sensitivity and 73/\$.ccls.) and (strain near	_	2003/08/25
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;			, ,		13:15
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;			·		
- 162268 73/\$.ccls. IBM_TDB USPAT; 2003/08/25 US-PGPUB; EPO; JPO;					
- 162268 73/\$.ccls. USPAT; 2003/08/25 US-PGPUB; EPO; JPO; 2003/08/25				•	
US-PGPUB; 15:56 EPO; JPO;	•	162268	73/\$.ccls.		2003/08/25
EPO; JPO;					
VERTERI:				DERWENT;	
IBM_TDB				· ·	

_	4339	strain near sens r	USPAT;	2003/08/25
-	7555	Strain near sens 1	US-P PUB;	13:15
!			EP; JP;	15.15
			DERWENT;	
			IBM_TDB	
	975	73/\$.ccls. and (strain n ar sensor)	_	2003/08/25
-	9/5	75/\$.ccis. and (strain it ar sensor)	USPAT;	13:15
			US-PGPUB;	13:15
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	468	sensitivity and (73/\$.ccls. and (strain near	USPAT;	2003/08/25
		sensor))	US-PGPUB;	13:42
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	18832	(touch contact) near sensor	USPAT;	2003/08/25
			US-PGPUB;	16:06
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
ļ -	46	(73/\$.ccls. and (strain near sensor)) and	USPAT;	2003/08/25
		((touch contact) near sensor)	US-PGPUB;	13:43
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	928	((touch contact) near sensor) and micron	USPAT;	2003/08/25
			US-PGPUB;	15:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	10	(strain near sensor) and (((touch contact)	USPAT;	2003/08/25
		near sensor) and micron)	US-PGPUB;	13:52
		,,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	77270	414/\$.ccis.	USPAT;	2003/08/25
			US-PGPUB;	16:06
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
l .	22990	(strain touch contact) near sensor	USPAT;	2003/08/25
		tariam taram asimuly man action	US-PGPUB;	15:57
			EPO; JPO;	
			DERWENT;	
	220	A4A/\$ colo and //strain touch contact\	IBM_TDB	2003/08/25
•	220	414/\$.ccls. and ((strain touch contact) near	USPAT;	16:11
		sensor)	US-PGPUB;	10:11
			EPO; JPO;	
			DERWENT;	
	L		IBM_TDB	

•	5	(414/\$.ccls. and ((strain touch c ntact) near	USPAT;	2003/08/25
		s nsor)) and micron	US-P PUB;	15:58
		·	EP ; JP ;	
			DERWENT;	
			IBM_TDB	
	12	("4449885" "4520421" "4565601"	USPAT	2003/08/25
		"4743570" "4892451" "4911597"		16:03
		"4962441" "4999507" "5007981"		
		"5113992" "5258047" "5315473").PN.		
	36806	294/\$.ccls.	USPAT;	2003/08/25
			US-PGPUB;	16:06
		,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	51	294/\$.ccls. and ((strain touch contact) near	USPAT;	2003/08/25
-		sensor)	US-PGPUB;	16:10
			EPO; JPO;	
•			DERWENT;	
			IBM_TDB	
_	5822	wafer near (blade chuck gripper)	USPAT;	2003/08/25
•	3622	water flear (blade clidck gripper)	US-PGPUB;	16:11
			EPO; JPO;	10.11
			DERWENT;	
	40	(water year (blade abusic gripper)) and	IBM_TDB	2003/08/25
-	49	(wafer near (blade chuck gripper)) and	USPAT;	16:11
		((strain touch contact) near sensor)	US-PGPUB;	10:11
			EPO; JPO;	
			DERWENT;	
	00040		IBM_TDB	2002/09/25
-	29618	strain near (sensor gauge)	USPAT;	2003/08/25 17:33
			US-PGPUB;	17:33
			EPO; JPO;	
			DERWENT;	
	5000		IBM_TDB	2002/00/25
•	5606	sensitivity same micron	USPAT;	2003/08/25
			US-PGPUB;	17:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/00/07
•	94	(strain near (sensor gauge)) and (sensitivity	USPAT;	2003/08/25
		same micron)	US-PGPUB;	17:38
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	116	(73/768).CCLS.	USPAT;	2003/08/25
			US-PGPUB;	17:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

•	524	piezo- lectric near sens r	USPAT;	2003/08/25
		•	US-PGPUB;	17:48
			EP ; JP ;	
			DERWENT;	
			IBM_TDB	
-	60	(strain near (sensor gauge)) and	USPAT;	2003/08/25
		(piezo-electric near sensor)	US-PGPUB;	17:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	1	((strain near (sensor gauge)) and	USPAT;	2003/08/25
		(piezo-electric near sensor)) and micron	US-PGPUB;	17:43
		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	5260	plezoelectric near sensor	USPAT;	2003/08/25
			US-PGPUB;	17:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	578	(strain near (sensor gauge)) and	USPAT;	2003/08/25
		(piezoelectric near sensor)	US-PGPUB;	17:48
		,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	143	((strain near (sensor gauge)) and	USPAT;	2003/08/25
		(plezoelectric near sensor)) and	US-PGPUB;	17:49
		(semiconductor wafer)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	145	(73/769).CCLS.	USPAT;	2003/08/25
		(US-PGPUB;	18:17
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	60	(73/770).CCLS.	USPAT;	2003/08/25
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	18:17
		·	EPO; JPO;	
			DERWENT;	
			IBM TDB	